1. Scope :

This specification applies to NIP silicon photodiode chips,
Device No. PD-40060C-B.

2. Structure :

2-1. Type : NIP diode.
2-2. Electrodes :
Top side (Cathode) : Aluminum alloy.
Back side (Anode) : Gold.

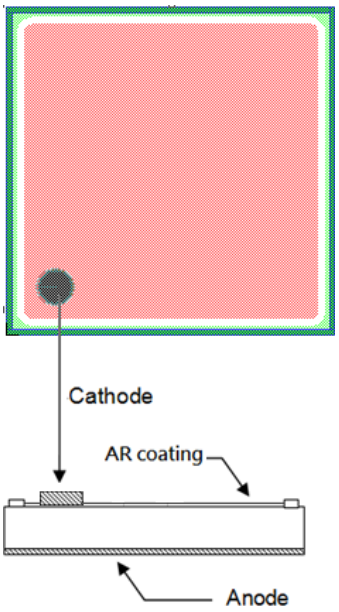
3. Size :

3-1. Chip size (including scribe lane): 60 mils x 60 mils (1.524 mm x 1.524 mm).
3-2. Chip thickness : 12 ± 1.0 mils (0.305mm ± 0.025 mm).
3-3. Active area : 53.7 mils x 53.7 mils (1.364 mm x 1.364 mm).
3-4. Bonding pad (Cathode) : 6.4 mils ± 0.394 mils (0.164 ± 0.010 mm) Diameter.
3-5. Pattern drawing : refer to the attached drawing

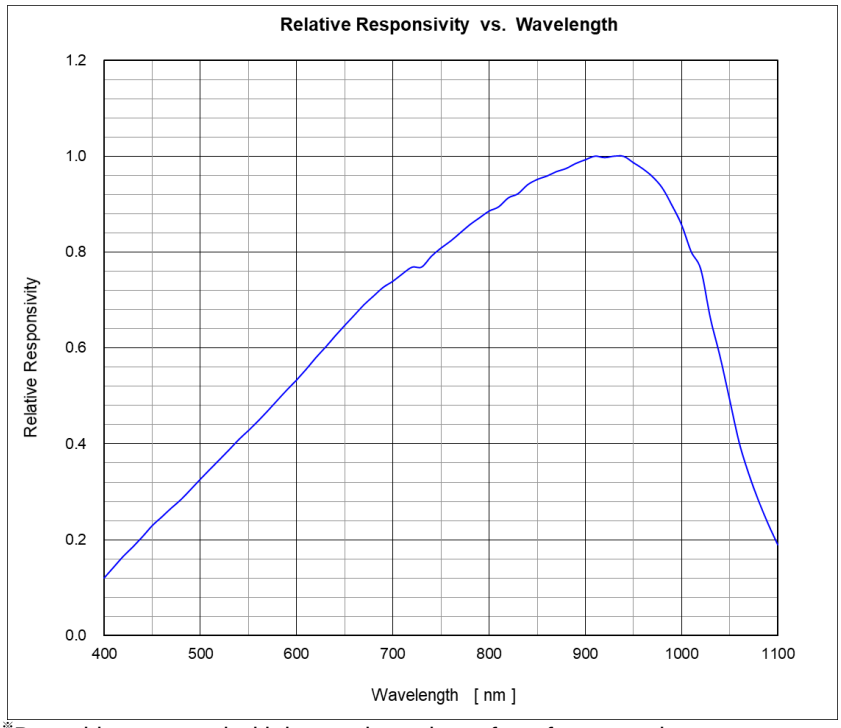
4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm^2	60			V
※Forward Voltage	V_F	I_F=10mA Ee=0mW/cm^2	0.7		1.3	V
Sensitivity	S	V_R =5V λ =940nm		0.8		A/W
Open circuit voltage	Voc	I_F =0mA λ =940nm Ee=127 mW/cm^2		400		mV
Short circuit Current	Isc	V_R =0V λ =940nm Ee=1 mW/cm^2		14.5		μA
Reverse light current	I_L	V_R =5V λ =940nm Ee=1 mW/cm^2		14.8		μA

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.